

Schottky Barrier Rectifier

MBR1060

FEATURES

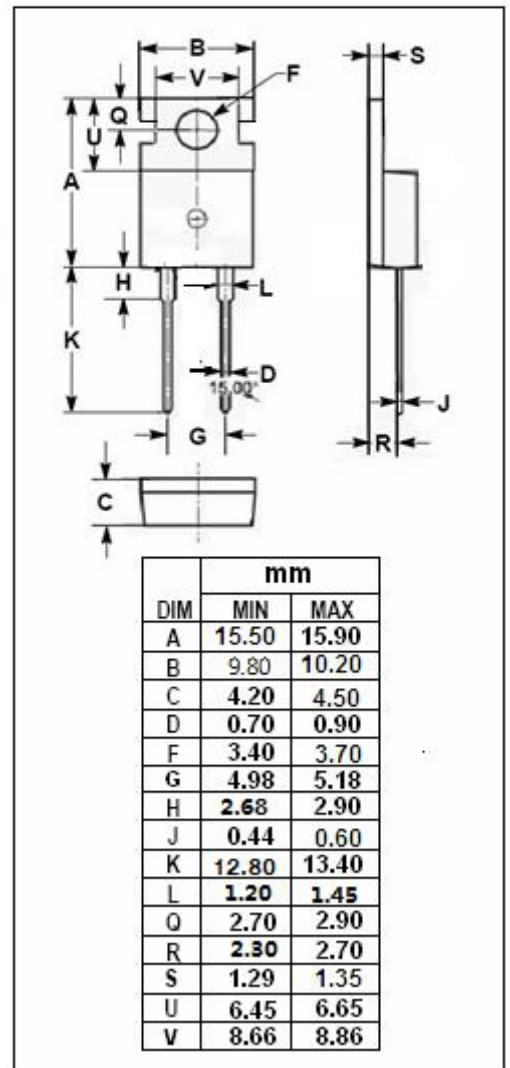
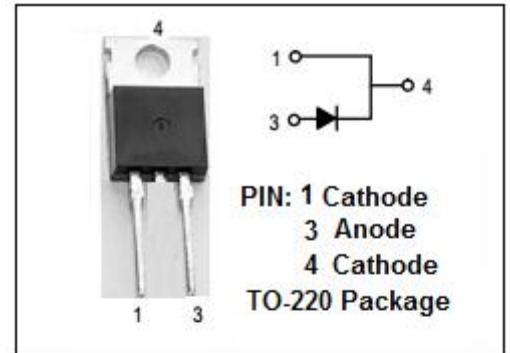
- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss/High Efficiency
- High Surge Capability
- High Current Capability, Low Forward Voltage Drop
- Plastic Material: UL Flammability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for low-voltage, high frequency inverters, free wheeling and polarity protection applications .

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{RRM} V _{RWM} V _R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	60	V
V _{R(RMS)}	RMS Reverse Voltag	42	V
I _{F(AV)}	Average Rectified Forward Current (Rated V _R) T _C = 125°C	10	A
I _{FSM}	Nonrepetitive Peak Surge Current (Surge applied at rated load conditions half-wave, single phase, 60Hz)	150	A
T _J	Junction Temperature	-65~150	°C
T _{stg}	Storage Temperature Range	-65~150	°C
dv/dt	Voltage Rate of Change (Rated V _R)	1000	V/μ s



Schottky Barrier Rectifier**MBR1060****THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	2.5	°C/W

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300 μ s, Duty Cycle ≤ 1%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V _F	Maximum Instantaneous Forward Voltage	I _F = 10A ; T _C = 25°C I _F = 10A ; T _C = 125°C	0.95 0.7	V
I _R	Maximum Instantaneous Reverse Current	Rated DC Voltage, T _C = 25°C Rated DC Voltage, T _C = 125°C	0.1 25	mA